

BRIEF SUMMARY OF THE INVENTION

[0003] The present invention is a method for improving the channel doping profile of deep-submicron field effect transistors and MOSFETs. By way of example, and not of limitation, the method involves a highly localized halo implant formed in the channel region but not in the source/drain junction. The halo implant is performed through a gap formed by removal of a temporary spacer. The MOSFET is then further completed.

[0004] The resultant device exhibits an increased operating speed over heretofore known similar devices. The instant method improves device density on the chip, enhancing the manufacturing precision and efficiency. Further objects and advantages of the invention will be brought out in the following portions of the specification, wherein the detailed description is for the purpose of fully disclosing preferred embodiments of the invention without placing limitations thereon.

BRIEF DESCRIPTION OF THE DRAWINGS

[0005] The invention will be more fully understood by reference to the following drawings which are for illustrative purposes only:

[0006] FIG. 1 is a schematic side view in cross-section of a semiconductor chip undergoing shallow source/drain extension implant.

[0007] FIG. 2 is a schematic side view in cross-section of the chip of FIG. 1 undergoing epitaxy and silicidization.

[0008] FIG. 3 is a schematic side view in cross-section of the chip of FIG. 2 after removal of the temporary spacer.

[0009] FIG. 4 is a schematic side view in cross-section of the chip of FIG. 3 undergoing a halo implant.

[0010] FIG. 5 is a schematic side view in cross-section of the chip of FIG. 4 undergoing subsequent MOSFET formation steps.

DETAILED DESCRIPTION OF THE INVENTION

[0011] Referring more specifically to the drawings, for illustrative purposes the present invention is embodied in the device and method generally shown in FIG. 1 through FIG. 5. It will be appreciated that the device may vary as to configuration and as to details of the components, and that the method may vary as to the specific steps and sequence, without departing from the basic concepts as disclosed herein.

[0012] The present invention method for improving the channel doping profile of deep-submicron field effect transistors and MOSFETs involves a single super halo implant in the channel/body of a MOSFET of approximately 50 nm or less. The method involves forming a gate stack having a spacer, forming source/drain regions by selective epitaxy, followed by creating a silicide on the source/drain regions and gate. The spacer is then removed and a super halo implant is performed through the space thus formed by removal of the spacer. The MOSFET is then further completed.

[0013] Referring first to FIG. 1, a substrate 1 having gate oxide 2, gate 3, liner oxide 4 and nitride spacer 5 is prepared in the conventional manner. Isolation trenches 6 are formed, and shallow source/drain junctions 11 are implanted with ions selected from the group consisting essentially of B^+ , BF_2^+ , As^+ , Sb^+ , P^+ , to a depth of approximately 10 nm to approximately 30 nm. Referring next to FIG. 2, a selective epitaxy is performed to form raised source/drain regions 12, followed by the formation of silicide 13 covering the source/drain regions 12 and gate 3.

[0014] As shown in FIG. 3, spacer 5 is then removed by wet chemistry such as hot phosphoric acid etch, leaving liner oxide 4. Removal of spacer 5 forms a void 21 on either side of gate 3. This void 21 allows for the implantation of a localized halo. Referring now to FIG. 4, a halo implant at an essentially vertical angle to a depth of approximately 40 nm to approximately 100 nm is then performed through void 21, using gate 3, silicide 13 and source/drain regions 12 as a mask. This halo implant of ions selected from the group

consisting essentially of B^+ , BF_2^+ , Ga^+ , In^+ , As^+ , Sb^+ , P^+ , forms a shallow halo 14 which is localized in the channel/body region of the FET.

[0015] Then, referring to FIG. 5, oxide layer 15 is deposited on the semiconductor chip. The chip is then planarized to form surface 18, then contacts 16 and metal lines 17 are formed. The remainder of the MOSFET is then completed in the normal fashion.

[0016] Although the description above contains many specificities, these should not be construed as limiting the scope of the invention but as merely providing illustrations of some of the presently preferred embodiments of this invention. Thus the scope of this invention should be determined by the appended claims and their legal equivalents. Therefore, it will be appreciated that the scope of the present invention fully encompasses other embodiments which may become obvious to those skilled in the art, and that the scope of the present invention is accordingly to be limited by nothing other than the appended claims, in which reference to an element in the singular is not intended to mean "one and only one" unless explicitly so stated, but rather "one or more." All structural, chemical, and functional equivalents to the elements of the above-described preferred embodiment that are known to those of ordinary skill in the art are expressly incorporated herein by reference and are intended to be encompassed by the present claims. Moreover, it is not necessary for a device or method to address each and every problem sought to be solved by the present invention, for it to be encompassed by the present claims. Furthermore, no element, component, or method step in the present disclosure is intended to be dedicated to the public regardless of whether the element, component, or method step is explicitly recited in the claims. No claim element herein is to be construed under the provisions of 35 U.S.C. 112, sixth paragraph, unless the element is expressly recited using the phrase "means for."